

1N4148  
1N4446  
1N4448

High-speed silicon diodes

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1N4448

**RATINGS**

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Continuous reverse voltage	$V_R$	max.	75 V
Repetitive peak reverse voltage	$V_{RRM}$	max.	75 V
Average rectified forward current	$I_F(AV)$	max.	150 mA
Forward current (d.c.)	$I_F$	max.	200 mA
Repetitive peak forward current	$I_{FRM}$	max.	450 mA
Non-repetitive peak forward current			
$t = 1 \mu s$			
$t = 1 s$			
Total power dissipation up to $T_{amb} = 25^\circ C$			
Derrating factor			2,85 mW/K
Storage temperature			
Junction temperature			

Derating factor

Storage temperature	$T_{stg}$	-65 to +200 °C
Junction temperature	$T_j$	max. 200 °C

**CHARACTERISTICS**

$T_j = 25^\circ C$  unless otherwise specified

Forward voltages

1N4148: $I_F = 10$ mA	$V_F$	<	1 V
1N4446: $I_F = 20$ mA			
1N4448: $I_F = 100$ mA			

1N4448:  $I_F = 5$  mA

Reverse avalanche breakdown voltage

$I_R = 100 \mu A$	$V_{(BR)R}$	>	100 V
$I_R = 5 \mu A$	$V_{(BR)R}$	>	75 V

Reverse currents

$V_R = 20$ V; $T_j = 100^\circ C$	$I_R$	<	25 nA
$V_R = 20$ V; $T_j = 150^\circ C$	$I_R$	<	3 $\mu A$
Diode capacitance	$I_R$	<	50 $\mu A$
$V_R = 0$ ; $f = 1$ MHz	$C_d$	<	4 pF

1N4448

**CHARACTERISTICS (continued)**

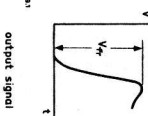
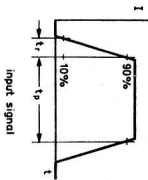
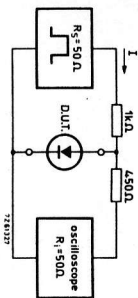
Forward recovery voltage when switched to

$I_F = 50$  mA;  $t_r = 20$  ns

$V_{FR} < 2,5$  V

$T_j = 25^\circ C$

Test circuit and waveforms:



Input signal : Rise time of the forward pulse

$t_r = 20$  ns

Forward current pulse duration

$t_p = 120$  ns

Duty factor

$\delta = 0,01$

Oscilloscope : Rise time

$t_r = 0,35$  ns

Circuit capacitance  $C \leq 1$  pF (C = oscilloscope input capacitance + parasitic capacitance)

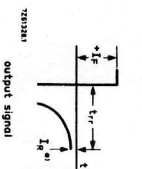
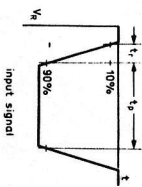
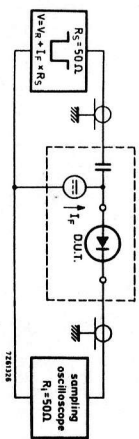
Reverse recovery time when switched from

$I_F = 10$  mA to  $I_R = 60$  mA;  $R_L = 100 \Omega$ ;

measured at  $I_R = 1$  mA

$t_{rr} < 4$  ns

Test circuit and waveforms:



Input signal : Rise time of the reverse pulse

$t_r = 0,6$  ns

Reverse pulse duration

$t_p = 100$  ns

Duty factor

$\delta = 0,05$

Oscilloscope : Rise time

$t_r = 0,35$  ns

(circuit capacitance  $C \leq 1$  pF (C = oscilloscope input capacitance + parasitic capacitance))

\*)  $I_R = 1$  mA